

Eric TourniÃ©

List of Publications by Year in descending order

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293
papers

5,163
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87886

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all docs

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docs citations

300
times ranked

3636
citing authors

#	ARTICLE	IF	CITATIONS
1	Crystal Phase Control during Epitaxial Hybridization of III-V Semiconductors with Silicon. <i>Advanced Electronic Materials</i> , 2022, 8, 2100777.	5.1	18
2	Impact of the ridge etching depth on GaSb-based laser diodes. <i>Electronics Letters</i> , 2022, 58, 162-163.	1.0	0
3	Characterization and Simulation of AlGaAsSb/GaSb Tandem Solar Cell. <i>IEEE Journal of Photovoltaics</i> , 2022, 12, 968-975.	2.5	1
4	Mid-infrared III-V semiconductor lasers epitaxially grown on Si substrates. <i>Light: Science and Applications</i> , 2022, 11, .	16.6	20
5	Investigation of AlInAsSb/GaSb tandem cells – A first step towards GaSb-based multi-junction solar cells. <i>Solar Energy Materials and Solar Cells</i> , 2021, 219, 110795.	6.2	9
6	GaSb-based laser diodes grown on MOCVD GaAs-on-Si templates. <i>Optics Express</i> , 2021, 29, 11268.	3.4	9
7	Thermal performance of GaInSb quantum well lasers for silicon photonics applications. <i>Applied Physics Letters</i> , 2021, 118, .	3.3	4
8	Near-Field Thermophotovoltaic Conversion with High Electrical Power Density and Cell Efficiency above 14%. <i>Nano Letters</i> , 2021, 21, 4524-4529.	9.1	79
9	Carrier recombination and temperature-dependence of GaInSb quantum well lasers for silicon photonics applications. , 2021, , .		0
10	Modeling and Characterization of an MBE-Grown Concentrator P-N GaSb Solar Cells Using a Pseudo-3D Model. <i>IEEE Journal of Photovoltaics</i> , 2021, 11, 1032-1039.	2.5	1
11	Selective Area Growth by Hydride Vapor Phase Epitaxy and Optical Properties of InAs Nanowire Arrays. <i>Crystal Growth and Design</i> , 2021, 21, 5158-5163.	3.0	5
12	Quantum well interband semiconductor lasers highly tolerant to dislocations. <i>Optica</i> , 2021, 8, 1397.	9.3	14
13	Carrier Recombination Processes in 2.3- μm Epitaxially Grown Mid-Infrared Laser Diodes on Si(001). , 2021, , .		0
14	Molecular-beam epitaxy of GaSb on 6 $^{\circ}$ -offcut (0 $\bar{1}0$) Si using a GaAs nucleation layer. <i>Journal of Crystal Growth</i> , 2020, 529, 125299.	1.5	6
15	Interband mid-infrared lasers. , 2020, , 91-130.		7
16	Optical properties and dynamics of excitons in Ga(Sb, Bi)/GaSb quantum wells: evidence for a regular alloy behavior. <i>Semiconductor Science and Technology</i> , 2020, 35, 025024.	2.0	3
17	Progress in Interband Cascade Lasers: From Edge Emitting Lasers to VCSELs. , 2020, , .		0
18	InAs-based quantum cascade lasers grown on on-axis (001) silicon substrate. <i>APL Photonics</i> , 2020, 5, .	5.7	22

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19	Morphological Control of InN Nanorods by Selective Area Growthâ€“Hydride Vapor-Phase Epitaxy. <i>Crystal Growth and Design</i> , 2020, 20, 2232-2239.	3.0	5
20	Zinc-blende group III-V/group IV epitaxy: Importance of the miscut. <i>Physical Review Materials</i> , 2020, 4, .	2.4	23
21	Etched-cavity GaSb laser diodes on a MOVPE GaSb-on-Si template. <i>Optics Express</i> , 2020, 28, 20785.	3.4	9
22	Mid-infrared laser diodes epitaxially grown on on-axis (001) silicon. <i>Optica</i> , 2020, 7, 263.	9.3	42
23	3.3 Åµm interband-cascade resonant-cavity light-emitting diode with narrow spectral emission linewidth. <i>Semiconductor Science and Technology</i> , 2020, 35, 125029.	2.0	6
24	Improved efficiency of GaSb solar cells using an Al _{0.50} Ga _{0.50} As _{0.04} Sb _{0.96} window layer. <i>Solar Energy Materials and Solar Cells</i> , 2019, 200, 110042.	6.2	14
25	The Interaction of Extended Defects as the Origin of Step Bunching in Epitaxial IIIâ€“V Layers on Vicinal Si(001) Substrates. <i>Physica Status Solidi - Rapid Research Letters</i> , 2019, 13, 1900290.	2.4	3
26	GaSbBi Alloys and Heterostructures: Fabrication and Properties. <i>Springer Series in Materials Science</i> , 2019, , 125-161.	0.6	1
27	Molecular-beam epitaxy of GaInSbBi alloys. <i>Journal of Applied Physics</i> , 2019, 126, .	2.5	6
28	Indium antimonide photovoltaic cells for near-field thermophotovoltaics. <i>Solar Energy Materials and Solar Cells</i> , 2019, 203, 110190.	6.2	15
29	Type I GaSb _{1-x} Bix/GaSb quantum wells dedicated for mid infrared laser applications: Photoreflectance studies of bandgap alignment. <i>Journal of Applied Physics</i> , 2019, 125, .	2.5	16
30	Terahertz Spectroscopy of Two-Dimensional Semimetal in Three-Layer InAs/GaSb/InAs Quantum Well. <i>JETP Letters</i> , 2019, 109, 96-101.	1.4	4
31	Selective growth of ordered hexagonal InN nanorods. <i>CrystEngComm</i> , 2019, 21, 2702-2708.	2.6	13
32	Massless Dirac fermions in III-V semiconductor quantum wells. <i>Physical Review B</i> , 2019, 99, .	3.2	14
33	Toward MIR VCSELs operating in CW at RT. , 2019, , .		0
34	InAs/GaSb thin layers directly grown on nominal (0â€“0â€“1)-Si substrate by MOVPE for the fabrication of InAs FINFET. <i>Journal of Crystal Growth</i> , 2019, 510, 18-22.	1.5	3
35	GaSb-based solar cells for multi-junction integration on Si substrates. <i>Solar Energy Materials and Solar Cells</i> , 2019, 191, 444-450.	6.2	13
36	Midwave infrared barrier detector based on Ga-free InAs/InAsSb type-II superlattice grown by molecular beam epitaxy on Si substrate. <i>Infrared Physics and Technology</i> , 2019, 96, 39-43.	2.9	29

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37	Micron-sized liquid nitrogen-cooled indium antimonide photovoltaic cell for near-field thermophotovoltaics. <i>Optics Express</i> , 2019, 27, A11.	3.4	31
38	Interband cascade Lasers with AlGaAsSb cladding layers emitting at 33â€…Åµm. <i>Optics Express</i> , 2019, 27, 31425.	3.4	10
39	Microstructure and interface analysis of emerging Ga(Sb,Bi) epilayers and Ga(Sb,Bi)/GaSb quantum wells for optoelectronic applications. <i>Applied Physics Letters</i> , 2018, 112, .	3.3	14
40	On the origin of threading dislocations during epitaxial growth of III-Sb on Si(001): A comprehensive transmission electron tomography and microscopy study. <i>Acta Materialia</i> , 2018, 143, 121-129.	7.9	12
41	Anti phase boundary free GaSb layer grown on 300 mm (001)-Si substrate by metal organic chemical vapor deposition. <i>Thin Solid Films</i> , 2018, 645, 5-9.	1.8	18
42	Pedestal formation of all-semiconductor gratings through GaSb oxidation for mid-IR plasmonics. <i>Journal Physics D: Applied Physics</i> , 2018, 51, 015104.	2.8	5
43	Quantum cascade lasers grown on silicon. , 2018, , .		0
44	Investigation of antimonide-based semiconductors for high-efficiency multi-junction solar cells. , 2018, , .		4
45	Interface energy analysis of IIIâ€œV islands on Si (001) in the Volmer-Weber growth mode. <i>Applied Physics Letters</i> , 2018, 113, .	3.3	14
46	Epitaxial Integration of Antimonide-Based Semiconductor Lasers on Si. <i>Semiconductors and Semimetals</i> , 2018, , 1-25.	0.7	2
47	A Stressâ€œFree and Textured GaP Template on Silicon for Solar Water Splitting. <i>Advanced Functional Materials</i> , 2018, 28, 1801585.	14.9	22
48	In situ determination of the growth conditions of GaSbBi alloys. <i>Journal of Crystal Growth</i> , 2018, 495, 9-13.	1.5	7
49	Phosphonate monolayers on InAsSb and GaSb surfaces for mid-IR plasmonics. <i>Applied Surface Science</i> , 2018, 451, 241-249.	6.1	12
50	Temperature-dependent terahertz spectroscopy of inverted-band three-layer InAs/GaSb/InAs quantum well. <i>Physical Review B</i> , 2018, 97, .	3.2	24
51	Transmission electron microscopy of Ga(Sb, Bi)/GaSb quantum wells with varying Bi content and quantum well thickness. <i>Semiconductor Science and Technology</i> , 2018, 33, 094006.	2.0	4
52	GaSb Lasers Grown on Silicon Substrate for Telecom Applications. , 2018, , 625-635.		2
53	Mid-IR plasmonic compound with gallium oxide toplayer formed by GaSb oxidation in water. <i>Semiconductor Science and Technology</i> , 2018, 33, 095009.	2.0	3
54	Quantum cascade lasers grown on silicon. <i>Scientific Reports</i> , 2018, 8, 7206.	3.3	56

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55	Universal description of III-V/Si epitaxial growth processes. <i>Physical Review Materials</i> , 2018, 2, .	2.4	43
56	AlInAsSb for GaSb-based multi-junction solar cells. , 2018, , .		3
57	LACBED analysis of the chemical composition of compound semiconductor strained layers. , 2018, , 221-224.		0
58	Electron tomography on III-Sb heterostructures on vicinal Si(001) substrates: Anti-phase boundaries as a sink for threading dislocations. <i>Scripta Materialia</i> , 2017, 132, 5-8.	5.2	9
59	Characterization of antimonide based material grown by molecular epitaxy on vicinal silicon substrates via a low temperature AlSb nucleation layer. <i>Journal of Crystal Growth</i> , 2017, 477, 65-71.	1.5	15
60	Growth and characterization of AlInAsSb layers lattice-matched to GaSb. <i>Journal of Crystal Growth</i> , 2017, 477, 72-76.	1.5	9
61	GaSbBi/GaSb quantum well laser diodes. <i>Applied Physics Letters</i> , 2017, 110, .	3.3	45
62	Molecular beam epitaxy and characterization of high Bi content GaSbBi alloys. <i>Journal of Crystal Growth</i> , 2017, 477, 144-148.	1.5	39
63	Highly doped semiconductor plasmonic nanoantenna arrays for polarization selective broadband surface-enhanced infrared absorption spectroscopy of vanillin. <i>Nanophotonics</i> , 2017, 7, 507-516.	6.0	33
64	III-V lasers epitaxially grown on Si. , 2017, , .		0
65	From 1-dimensional to 2-dimensional periodic semiconductor plasmonic resonators: Designing the optical response for sensing applications. , 2017, , .		0
66	Magnetoabsorption of Dirac Fermions in InAs/GaSb/InAs "Three-Layer" Gapless Quantum Wells. <i>JETP Letters</i> , 2017, 106, 727-732.	1.4	5
67	Low-loss orientation-patterned GaSb waveguides for mid-infrared parametric conversion. <i>Optical Materials Express</i> , 2017, 7, 3011.	3.0	14
68	Surface-enhanced infrared absorption with Si-doped InAsSb/GaSb nano-antennas. <i>Optics Express</i> , 2017, 25, 26651.	3.4	15
69	Room-temperature continuous-wave operation in the telecom wavelength range of GaSb-based lasers monolithically grown on Si. <i>APL Photonics</i> , 2017, 2, .	5.7	36
70	Plasmonic bio-sensing based on highly doped semiconductors. , 2017, , .		2
71	Anisotropic strain relaxation and growth mode dependence in highly lattice mismatched III-V systems. , 2017, , 389-392.		0
72	First orientation-patterned GaSb ridge waveguides fabrication and preliminary characterization for frequency conversion in the mid-infrared. <i>Proceedings of SPIE</i> , 2016, , .	0.8	1

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73	Metamorphic III-V semiconductor lasers grown on silicon. MRS Bulletin, 2016, 41, 218-223.	3.5	47
74	Localized surface plasmon resonance frequency tuning in highly doped InAsSb/GaSb one-dimensional nanostructures. Nanotechnology, 2016, 27, 425201.	2.6	23
75	GaSb lasers grown on Silicon substrate emitting in the telecom wavelength range. , 2016, , .		0
76	X-ray diffraction study of GaSb grown by molecular beam epitaxy on silicon substrates. Journal of Crystal Growth, 2016, 439, 33-39.	1.5	32
77	Terahertz studies of 2D and 3D topological transitions. Journal of Physics: Conference Series, 2015, 647, 012037.	0.4	0
78	Mid-infrared characterization of refractive indices and propagation losses in GaSb/AlXGa1-XAsSb waveguides. Applied Physics Letters, 2015, 107, .	3.3	15
79	GaSb-based composite quantum wells for laser diodes operating in the telecom wavelength range near 1.55- μm . Applied Physics Letters, 2015, 106, .	3.3	12
80	Observation of Fano resonances in highly doped semiconductor plasmonic resonators (Presentation) Tj ETQq0 0 0 rgBT /Overlock 10 T	0.8	0
81	Fano-like resonances sustained by Si doped InAsSb plasmonic resonators integrated in GaSb matrix. Optics Express, 2015, 23, 29423.	3.4	10
82	Silicon surface preparation for III-V molecular beam epitaxy. Journal of Crystal Growth, 2015, 413, 17-24.	1.5	27
83	M-lines characterization of the refractive index of GaSb and AlXGa1-XAsSb lattice-matched onto GaSb in the mid-infrared. , 2015, , .		0
84	Silicon-on-insulator shortwave infrared wavelength meter with integrated photodiodes for on-chip laser monitoring. Optics Express, 2014, 22, 27300.	3.4	26
85	Brewster mode in highly doped semiconductor layers: an all-optical technique to monitor doping concentration. Optics Express, 2014, 22, 24294.	3.4	54
86	Long-wavelength silicon photonic integrated circuits. , 2014, , .		0
87	Silicon-Based Photonic Integration Beyond the Telecommunication Wavelength Range. IEEE Journal of Selected Topics in Quantum Electronics, 2014, 20, 394-404.	2.9	106
88	Recombination channels in 2.4-3.2 μm GaInAsSb quantum-well lasers. Semiconductor Science and Technology, 2013, 28, 015015.	2.0	17
89	Mid-IR heterogeneous silicon photonics. Proceedings of SPIE, 2013, , .	0.8	2
90	Mid-IR GaSb-Based Bipolar Cascade VCSELs. IEEE Photonics Technology Letters, 2013, 25, 882-884.	2.5	14

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91	Effects of low temperature on the cold start gaseous emissions from light duty vehicles fuelled by ethanol-blended gasoline. Applied Energy, 2013, 102, 44-54.	10.1	140
92	All-semiconductor plasmonics for mid-IR applications. , 2013, , .		3
93	Silicon-on-insulator spectrometers with integrated GaInAsSb photodiodes for wide-band spectroscopy from 1510 to 2300 nm. Optics Express, 2013, 21, 6101.	3.4	82
94	Silicon-based heterogeneous photonic integrated circuits for the mid-infrared. Optical Materials Express, 2013, 3, 1523.	3.0	65
95	Mid-IR GaSb-based monolithic vertical-cavity surface-emitting lasers. Journal Physics D: Applied Physics, 2013, 46, 495101.	2.8	6
96	GaSb-based all-semiconductor mid-IR plasmonics. , 2013, , .		3
97	Integrated thin-film GaSb-based Fabry-Perot lasers: towards a fully integrated spectrometer on a SOI waveguide circuit. , 2013, , .		5
98	Atomic structure of tensile-strained GaAs/GaSb(001) nanostructures. Applied Physics Letters, 2013, 102, .	3.3	7
99	Silicon-on-Insulator spectrometers with integrated GaInAsSb photodiode array for wideband operation from 1500 to 2300 nm.. , 2013, , .		0
100	Selective lateral etching of InAs/GaSb tunnel junctions for mid-infrared photonics. Semiconductor Science and Technology, 2012, 27, 085011.	2.0	8
101	Study of evanescently-coupled and grating-assisted GaInAsSb photodiodes integrated on a silicon photonic chip. Optics Express, 2012, 20, 11665.	3.4	51
102	Single-Mode Monolithic GaSb Vertical-Cavity Surface-Emitting Laser. Optics Express, 2012, 20, 15540.	3.4	22
103	Localized surface plasmon resonances in highly doped semiconductors nanostructures. Applied Physics Letters, 2012, 101, .	3.3	58
104	Integrated spectrometer and integrated detectors on Silicon-on-Insulator for short-wave infrared applications. , 2012, , .		1
105	High temperature continuous wave operation of Sb-based monolithic EP-VCSEL with Selectively Etched Tunnel-Junction Apertures. , 2012, , .		0
106	Mid-Infrared Semiconductor Lasers. Semiconductors and Semimetals, 2012, , 183-226.	0.7	42
107	Pseudo volume plasmon in arrays of doped and un-doped semiconductors. Applied Physics A: Materials Science and Processing, 2012, 109, 927-934.	2.3	0
108	Arrays of doped and un-doped semiconductors for sensor applications. Applied Physics A: Materials Science and Processing, 2012, 109, 943-947.	2.3	3

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109	Online characterization of regulated and unregulated gaseous and particulate exhaust emissions from two-stroke mopeds: A chemometric approach. <i>Analytica Chimica Acta</i> , 2012, 717, 28-38.	5.4	39
110	GaSb-based integrated lasers and photodetectors on a Silicon-On-Insulator waveguide circuit for sensing applications in the shortwave infrared. , 2012, , .		6
111	GaSb-based laser monolithically grown on Si substrate by molecular beam epitaxy. , 2012, , .		0
112	IIIâ€V/Silicon Photonics for Short-Wave Infrared Spectroscopy. <i>IEEE Journal of Quantum Electronics</i> , 2012, 48, 292-298.	1.9	8
113	Heterogeneous Integration of GaInAsSb p-i-n Photodiodes on a Silicon-on-Insulator Waveguide Circuit. <i>IEEE Photonics Technology Letters</i> , 2011, 23, 1760-1762.	2.5	34
114	Note: A high transmission Faraday optical isolator in the 9.2 μ m range. <i>Review of Scientific Instruments</i> , 2011, 82, 096106.	1.3	8
115	Heterogeneous GaSb/SOI mid-infrared photonic integrated circuits for spectroscopic applications. , 2011, , .		3
116	Continuous-wave operation above room temperature of GaSb-based laser diodes grown on Si. <i>Applied Physics Letters</i> , 2011, 99, .	3.3	78
117	Heterogeneously integrated InGaAsSb detectors on SOI waveguide circuits for short-wave infrared applications. , 2011, , .		0
118	Non-random Be-to-Zn substitution in ZnBeSe alloys: Raman scattering and ab initio calculations. <i>European Physical Journal B</i> , 2010, 73, 461-469.	1.5	9
119	Sb-based laser sources grown by molecular beam epitaxy on silicon substrates. <i>Proceedings of SPIE</i> , 2010, , .	0.8	0
120	Interfacial intermixing in InAs/GaSb short-period-superlattices grown by molecular beam epitaxy. <i>Applied Physics Letters</i> , 2010, 96, .	3.3	44
121	Highly tensile-strained, type-II, Ga $_{1-x}$ In $_x$ As/GaSb quantum wells. <i>Applied Physics Letters</i> , 2010, 96, .	3.3	12
122	GaSb-Based Laser, Monolithically Grown on Silicon Substrate, Emitting at 1.55 μ m at Room Temperature. <i>IEEE Photonics Technology Letters</i> , 2010, 22, 553-555.	2.5	67
123	Optical performances of InAs/GaSb/InSb short-period superlattice laser diode for mid-infrared emission. <i>Journal of Applied Physics</i> , 2010, 108, 093107.	2.5	14
124	Modelling of an InAs/GaSb/InSb short-period superlattice laser diode for mid-infrared emission by the k.p method. <i>Journal Physics D: Applied Physics</i> , 2010, 43, 325102.	2.8	14
125	GaSb-based mid-IR electrically-pumped VCSELs covering the wavelength range from 2.3 to 2.7 μ m. , 2009, , .		0
126	InAs/GaSb/InSb short-period super-lattice diode lasers emitting near 3.3 μ m at room-temperature. <i>Electronics Letters</i> , 2009, 45, 165.	1.0	11

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127	Interface properties of (Ga,In)(N,As) and (Ga,In)(As,Sb) materials systems grown by molecular beam epitaxy. Journal of Crystal Growth, 2009, 311, 1739-1744.	1.5	23
128	MBE growth of mid-IR diode lasers based on InAs/GaSb/InSb short-period superlattice active zones. Journal of Crystal Growth, 2009, 311, 1905-1907.	1.5	6
129	GaSb-based VCSELs emitting in the mid-infrared wavelength range ($2\text{--}3\ \mu\text{m}$) grown by MBE. Journal of Crystal Growth, 2009, 311, 1912-1916.	1.5	29
130	Mid-infrared GaSb-based EP-VCSEL emitting at $2.63\ \mu\text{m}$. Electronics Letters, 2009, 45, 265.	1.0	33
131	Room-temperature operation of a $2.25\ \mu\text{m}$ electrically pumped laser fabricated on a silicon substrate. Applied Physics Letters, 2009, 94, .	3.3	37
132	Mid-IR lasing from highly tensile-strained, type II, GaInAs/GaSb quantum wells. Electronics Letters, 2009, 45, 1320.	1.0	5
133	GaSb-based, $2.2\ \mu\text{m}$ type-I laser fabricated on GaAs substrate operating continuous wave at room temperature. Applied Physics Letters, 2009, 94, 023506.	3.3	40
134	Room temperature, continuous wave operation of an Sb-based laser grown on GaAs substrate. , 2009, , .		0
135	Demonstration of laser operation at room-temperature of an Sb-based mid-infrared multi-quantum-well structure monolithically grown on a Silicon substrate. , 2009, , .		0
136	Subpicosecond timescale carrier dynamics in GaInAsSb/AlGaAsSb double quantum wells emitting at $2.3\ \mu\text{m}$. Applied Physics Letters, 2008, 92, .	3.3	20
137	S20 photocathodes grown by molecular-beam deposition. Electronics Letters, 2008, 44, 315.	1.0	1
138	Type II transition in InSb-based nanostructures for midinfrared applications. Journal of Applied Physics, 2008, 103, 114516.	2.5	9
139	Transmission Electron Microscopy Study of Sb-Based Quantum Dots. Springer Proceedings in Physics, 2008, , 251-254.	0.2	0
140	InAs/GaSb short-period superlattice injection lasers operating in $2.5\text{--}3.5\ \mu\text{m}$ mid-infrared wavelength range. Electronics Letters, 2007, 43, 1285.	1.0	15
141	InSb/GaSb self-assembled quantum dots. Physical R	3.2	9
142	Molecular-beam epitaxy of InSb/GaSb quantum dots. Journal of Applied Physics, 2007, 101, 124309.	2.5	31
143	High-density InSb-based quantum dots emitting in the mid-infrared. Journal of Crystal Growth, 2007, 301-302, 713-717.	1.5	18
144	Growth and characterization of GaInSb/GaInAsSb hole-well laser diodes emitting near $2.93\ \mu\text{m}$. Journal of Crystal Growth, 2007, 301-302, 967-970.	1.5	3

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145	Interface analysis of InAs/GaSb superlattice grown by MBE. Journal of Crystal Growth, 2007, 301-302, 889-892.	1.5	47
146	Investigations of InSb-based quantum dots grown by molecular-beam epitaxy. Physica Status Solidi C: Current Topics in Solid State Physics, 2007, 4, 1743-1746.	0.8	1
147	MBE growth and interface formation of compound semiconductor heterostructures for optoelectronics. Physica Status Solidi (B): Basic Research, 2007, 244, 2683-2696.	1.5	11
148	Structural and optical properties of InSb quantum dots for mid-IR applications. Physica Status Solidi (B): Basic Research, 2006, 243, 3959-3962.	1.5	8
149	Correlation between quantum well morphology, carrier localization and the optoelectronic properties of GaInNAs/GaAs light emitting diodes. Semiconductor Science and Technology, 2006, 21, 1047-1052.	2.0	5
150	High-density, uniform InSb ^δ -GaSb quantum dots emitting in the midinfrared region. Applied Physics Letters, 2006, 89, 263118.	3.3	26
151	720 mW continuous wave room temperature operation diode laser emitting at around 2.4 μ m. , 2005, 5989, 81.		1
152	LO multi-phonons cooperative phenomenon in ZnSe ^δ -BeSemixed crystals. Journal of Physics and Chemistry of Solids, 2005, 66, 2099-2103.	4.0	4
153	Percolation picture for long wavelength phonons in zinc blende alloys: application to GaInAs. Journal of Physics and Chemistry of Solids, 2005, 66, 2094-2098.	4.0	0
154	Decomposition in as-grown (Ga,In)(N,As) quantum wells. Applied Physics Letters, 2005, 87, 171901.	3.3	40
155	Correlation between interface structure and light emission at 1.3 μ -1.55 μ m of (Ga,In)(N,As) diluted nitride heterostructures on GaAs substrates. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2004, 22, 2195.	1.6	34
156	Long-wave phonons in ZnSe ^δ -BeSemixed crystals: Raman scattering and percolation model. Physical Review B, 2004, 70, .	3.2	28
157	Be ^δ -Se double-phonon behavior in Zn _{1-x} Be _y BexSe alloy. Journal of Applied Physics, 2004, 95, 7690-7693.	2.5	4
158	Carrier recombination processes in GaAsN: from the dilute limit to alloying. IEE Proceedings: Optoelectronics, 2004, 151, 365-368.	0.8	4
159	Percolation-based multimode Ga ^δ -N behaviour in the Raman spectra of GaInAsN. IEE Proceedings: Optoelectronics, 2004, 151, 338-341.	0.8	0
160	Giant LO oscillation in the Zn _{1-x} Bex(S _e ,T _e) multi-phonons percolative alloys. Thin Solid Films, 2004, 450, 195-198.	1.8	5
161	Does In-bonding delay GaN-segregation in GaInAsN? A Raman study. Applied Physics Letters, 2004, 85, 5872-5874.	3.3	11
162	Nanoscale analysis of the In and N spatial redistributions upon annealing of GaInNAs quantum wells. Applied Physics Letters, 2004, 84, 2503-2505.	3.3	57

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163	From GaAs:N to oversaturated GaAsN: Analysis of the band-gap reduction. Physical Review B, 2004, 69, .	3.2	34
164	Dominant carrier recombination mechanisms in GaInNAs/GaAs quantum well light-emitting diodes. Applied Physics Letters, 2004, 85, 40-42.	3.3	7
165	Bi-modal Raman response of BeSe vibration in Zn _{1-x} Mg _x BeSe alloys. Journal of Alloys and Compounds, 2004, 382, 271-274.	5.5	7
166	Effect of nitrogen on the band structure and material gain of In _y Ga _{1-y} As _{1-x} N _x /GaAs quantum wells. IEEE Journal of Selected Topics in Quantum Electronics, 2003, 9, 716-722.	2.9	16
167	Correlations between structural and optical properties of GaInNAs quantum wells grown by MBE. Journal of Crystal Growth, 2003, 251, 383-387.	1.5	31
168	Percolation context in mixed crystals with mechanical contrast. Journal of Physics and Chemistry of Solids, 2003, 64, 1585-1590.	4.0	2
169	LO phonon-plasmon coupling and mechanical disorder-induced effect in the Raman spectra of GaAsN alloys. Solid-State Electronics, 2003, 47, 455-460.	1.4	5
170	Photoluminescence spectroscopy of Ga(In)NAs quantum wells for emission at 1.5 μ m. Solid-State Electronics, 2003, 47, 477-482.	1.4	11
171	Coexistence in photoluminescence of free exciton and bound exciton in low nitrogen content GaInNAs layers. Physica Status Solidi C: Current Topics in Solid State Physics, 2003, 0, 2631-2634.	0.8	0
172	Nanoindentation of Si, GaP, GaAs and ZnSe single crystals. Journal Physics D: Applied Physics, 2003, 36, L5-L9.	2.8	74
173	Annealing effects on the crystal structure of GaInNAs quantum wells with large In and N content grown by molecular beam epitaxy. Journal of Applied Physics, 2003, 94, 2319-2324.	2.5	60
174	GaInNAs/GaAs quantum wells grown by molecular-beam epitaxy emitting above 1.5 μ m. Applied Physics Letters, 2003, 82, 1845-1847.	3.3	38
175	Percolation-based vibrational picture to estimate nonrandom N substitution in GaAsN alloys. Applied Physics Letters, 2003, 82, 2808-2810.	3.3	18
176	Isoelectronic traps in heavily doped GaAs:(In,N). Physical Review B, 2003, 68, .	3.2	14
177	Interplay between the growth temperature, microstructure, and optical properties of GaInNAs quantum wells. Applied Physics Letters, 2003, 82, 3451-3453.	3.3	36
178	Mechanisms affecting the photoluminescence spectra of GaInNAs after post-growth annealing. Applied Physics Letters, 2002, 80, 4148-4150.	3.3	85
179	Nanoindentation study of Zn _{1-x} Be _x Se heteroepitaxial layers. Journal Physics D: Applied Physics, 2002, 35, 3015-3020.	2.8	24
180	Raman study of Zn _{1-x} Be _x Se/GaAs systems with low Be content ($x \leq 0.20$). Journal of Applied Physics, 2002, 91, 9187-9197.	2.5	14

#	ARTICLE	IF	CITATIONS
181	Raman study of Zn _{1-x} Be _x Se/GaAs systems with low Be-content (x=0.31). Thin Solid Films, 2002, 403-404, 530-534.	1.8	1
182	LO phonon-plasmon coupling in N-doped Zn _{1-x} Be _x Se/GaAs (x=0.15). Thin Solid Films, 2002, 403-404, 535-538.	1.8	0
183	Vibrational Evidence for Percolative Behavior in ZnBeSe. Physica Status Solidi (B): Basic Research, 2002, 229, 25-29.	1.5	7
184	Self-Compensation of the Phosphorus Acceptor in ZnSe. Physica Status Solidi (B): Basic Research, 2002, 229, 251-255.	1.5	3
185	Displaced Substitutional Phosphorus Acceptors in Zinc Selenide. Physica Status Solidi (B): Basic Research, 2002, 229, 257-260.	1.5	4
186	Light-Hole and Heavy-Hole Excitons: the Right Probe for the Physics of Low N Content GaAsN. Physica Status Solidi (B): Basic Research, 2002, 234, 778-781.	1.5	1
187	Electronic structure and radiative lifetimes of ideal Zn _{1-x} Be _x Se alloys. Solid State Communications, 2002, 123, 209-212.	1.9	11
188	Evaluation of the potential of ZnSe and Zn(Mg)BeSe compounds for ultraviolet photodetection. IEEE Journal of Quantum Electronics, 2001, 37, 1146-1152.	1.9	37
189	Raman study of Zn _x Be _{1-x} Se solid solutions. Optical Materials, 2001, 17, 323-326.	3.6	6
190	Wide-band-gap ZnMgBeSe alloys grown onto GaAs by molecular beam epitaxy. Journal of Crystal Growth, 2001, 223, 461-465.	1.5	8
191	Direct evidence for the trigonal symmetry of shallow phosphorus acceptors in ZnSe. Physical Review B, 2001, 64, .	3.2	9
192	On the origin of carrier localization in Ga _{1-x} In _x NyAs _{1-y} /GaAs quantum wells. Applied Physics Letters, 2001, 78, 1562-1564.	3.3	130
193	Visible-blind ultraviolet photodetectors based on ZnMgBeSe Schottky barrier diodes. Applied Physics Letters, 2001, 78, 4190-4192.	3.3	29
194	Vibrational evidence for a percolative behavior in Zn _{1-x} Be _x Se. Physical Review B, 2001, 65, .	3.2	37
195	Influence of alloy stability on the photoluminescence properties of GaAsN/GaAs quantum wells grown by molecular beam epitaxy. Applied Physics Letters, 2001, 79, 3404-3406.	3.3	40
196	ZnSe- and ZnMgBeSe-Based Schottky Barrier Photodetectors for the Blue and Ultraviolet Spectral Range. Physica Status Solidi A, 2000, 180, 301-305.	1.7	3
197	Molecular beam epitaxial growth and characterization of Be(Zn)Se on Si(001) and GaAs(001). Journal of Crystal Growth, 2000, 214-215, 95-99.	1.5	11
198	Hydrogen/deuterium: a probe to investigate carrier-compensation in ZnSe:N. Journal of Crystal Growth, 2000, 214-215, 507-510.	1.5	3

#	ARTICLE	IF	CITATIONS
199	ZnSe-based heterostructures for blue-green lasers. <i>Comptes Rendus Physique</i> , 2000, 1, 23-33.	0.1	2
200	Molecular beam epitaxy of $Zn_xBe_{1-x}Se$: Influence of the substrate nature and epilayer properties. <i>Journal of Electronic Materials</i> , 2000, 29, 883-886.	2.2	6
201	ZnSe-based Schottky barrier photodetectors. <i>Electronics Letters</i> , 2000, 36, 352.	1.0	19
202	Transmission electron microscopy study of crystal defects in ZnSe/GaAs(001) epilayers. <i>Journal of Physics Condensed Matter</i> , 2000, 12, 10287-10293.	1.8	6
203	Long wavelength GaInNAs/GaAs quantum-well heterostructures grown by solid-source molecular-beam epitaxy. <i>Applied Physics Letters</i> , 2000, 77, 2189-2191.	3.3	42
204	Zn(Mg)BeSe-based p-i-n photodiodes operating in the blue-violet and near-ultraviolet spectral range. <i>Applied Physics Letters</i> , 2000, 76, 242-244.	3.3	23
205	Spectroscopy of the phosphorus impurity in ZnSe epitaxial layers grown by molecular-beam epitaxy. <i>Physical Review B</i> , 2000, 61, 15789-15796.	3.2	22
206	Spectroscopy of the interaction between nitrogen and hydrogen in ZnSe epitaxial layers. <i>Physical Review B</i> , 2000, 62, 12868-12874.	3.2	4
207	Raman study of $Zn_xBe_{1-x}Se$ alloy (100) epitaxial layers. <i>Applied Physics Letters</i> , 2000, 77, 519-521.	3.3	25
208	Native vacancies in nitrogen-doped and undoped ZnSe layers studied by positron annihilation. <i>Physical Review B</i> , 2000, 62, 15711-15717.	3.2	8
209	Study of the band alignment in $(Zn,\delta Cd)Se/ZnSe$ quantum wells by means of photoluminescence excitation spectroscopy. <i>Journal of Applied Physics</i> , 2000, 87, 1863-1868.	2.5	7
210	Nature of the band gap in $Zn_{1-x}Be_xSe$ alloys. <i>Physical Review B</i> , 2000, 61, 5332-5336.	3.2	47
211	Ohmic contacts to p-type ZnSe using a ZnSe/BeTe superlattice. <i>Applied Physics Letters</i> , 1999, 75, 3345-3347.	3.3	11
212	Evidence of N-related compensating donors in lightly doped ZnSe:N. <i>Applied Physics Letters</i> , 1999, 74, 2200-2202.	3.3	17
213	Interactions of intentionally diffused hydrogen with nitrogen acceptors and nitrogen related donor centers in molecular beam epitaxy grown ZnSe. <i>Journal of Applied Physics</i> , 1999, 86, 1393-1397.	2.5	4
214	p-type doping of Zn(Mg)BeSe epitaxial layers. <i>Applied Physics Letters</i> , 1999, 75, 382-384.	3.3	14
215	Molecular-beam epitaxy of BeTe layers on GaAs substrates. <i>Journal of Crystal Growth</i> , 1999, 201-202, 494-497.	1.5	1
216	Investigations by high-resolution X-ray diffraction (HRXRD) and transmission electron microscopy (TEM) of $(BeTe/ZnSe)$ superlattices grown by molecular beam epitaxy onto GaAs buffer epilayer. <i>Journal of Crystal Growth</i> , 1999, 201-202, 498-501.	1.5	6

#	ARTICLE	IF	CITATIONS
217	Molecular-beam epitaxy of $Zn_xBe_{1-x}Se$ layers on vicinal Si(001) substrates. Journal of Crystal Growth, 1999, 201-202, 514-517.	1.5	6
218	p-Type doping of ZnSe and related materials controlled by diluting nitrogen in an inert gas. Journal of Crystal Growth, 1999, 201-202, 938-941.	1.5	3
219	New developments in the heteroepitaxial growth of Be-chalcogenides based semiconducting alloys. Journal of Electronic Materials, 1999, 28, 662-665.	2.2	11
220	The phosphorus acceptor in ZnSe. Journal of Crystal Growth, 1998, 184-185, 515-519.	1.5	12
221	The nitrogen-related shallow donor in ZnSe : N epitaxial layers. Journal of Crystal Growth, 1998, 184-185, 520-524.	1.5	7
222	A study of luminescence thermal quenching in ZnCdSe/ZnSse quantum wells for the optimal design of blue laser structures. Journal of Crystal Growth, 1998, 184-185, 591-595.	1.5	3
223	Band offset determination of the $Zn_{1-x}Cd_xSe/ZnSe$ interface. Journal of Crystal Growth, 1998, 184-185, 839-843.	1.5	5
224	New results on the solid-phase recrystallisation of ZnSe. Journal of Crystal Growth, 1998, 184-185, 1021-1025.	1.5	13
225	Hetero-epitaxial growth of $BexZn_{1-x}Se$ on Si(0 0 1) and GaAs(0 0 1) substrates. Journal of Crystal Growth, 1998, 184-185, 11-15.	1.5	32
226	Defect density in ZnSe pseudomorphic layers grown by molecular beam epitaxy on to various GaAs buffer layers. Journal of Crystal Growth, 1998, 192, 102-108.	1.5	18
227	New results and trends in the solid phase recrystallization of ZnSe. Materials Letters, 1998, 36, 162-166.	2.6	11
228	Critical thickness of $Zn_{1-x}Cd_xSe/ZnSe$ heterostructures grown on relaxed ZnSe buffer layers on bare GaAs substrates. Applied Physics Letters, 1998, 72, 217-219.	3.3	5
229	Heteroepitaxial growth of BeSe on vicinal Si(001) surfaces. Applied Physics Letters, 1998, 73, 957-959.	3.3	15
230	Anisotropic misfit dislocation nucleation in two-dimensional grown InAs/GaAs(001) heterostructures. Applied Physics Letters, 1998, 73, 1074-1076.	3.3	17
231	Molecular-beam epitaxy of BeTe layers on GaAs substrates studied via reflection high-energy electron diffraction. Applied Physics Letters, 1998, 72, 2859-2861.	3.3	11
232	Scattered light noise in gravitational wave interferometric detectors: A statistical approach. Physical Review D, 1997, 56, 6085-6095.	4.7	47
233	Self-compensation in nitrogen-doped ZnSe. Physical Review B, 1997, 56, R1657-R1660.	3.2	22
234	(001) GaAs substrate preparation for direct ZnSe heteroepitaxy. Journal of Applied Physics, 1997, 81, 7012-7017.	2.5	14

#	ARTICLE	IF	CITATIONS
235	Structural and optical properties of lattice-matched ZnBeSe layers grown by molecular-beam epitaxy onto GaAs substrates. Applied Physics Letters, 1997, 70, 3564-3566.	3.3	37
236	Issues in molecular-beam epitaxy of ZnSe-based heterostructures for blue-green lasers. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1997, 43, 21-28.	3.5	11
237	Exciton Relaxation Dynamics in (Zn, Cd)Se/ZnSe Quantum Well. Physica Status Solidi A, 1997, 164, 217-220.	1.7	1
238	ZnSe homoepitaxial growth on solid-phase recrystallized substrates. Journal of Crystal Growth, 1997, 175-176, 577-582.	1.5	7
239	Simulations of heteroepitaxial growth. Journal of Crystal Growth, 1997, 178, 258-267.	1.5	33
240	Microstructural study of pseudomorphic ZnSe films grown on bare GaAs substrates. Journal of Crystal Growth, 1997, 182, 45-52.	1.5	5
241	Photoluminescence study of ZnSe single crystals grown by solid-phase recrystallization. Applied Physics Letters, 1996, 68, 1356-1358.	3.3	41
242	Spectroscopy of biexcitons in strained-layer quantum wells. Journal of Crystal Growth, 1996, 159, 546-550.	1.5	2
243	Structural and optical characterization of ZnSe single crystals grown by solid-phase recrystallization. Journal of Applied Physics, 1996, 80, 2983-2989.	2.5	44
244	Molecular-beam epitaxy of high-quality ZnSe homoepitaxial layers on solid-phase recrystallized substrates. Applied Physics Letters, 1996, 69, 3221-3223.	3.3	12
245	Spectroscopy of donor-acceptor pairs in nitrogen-doped ZnSe. Physical Review B, 1996, 54, 4714-4721.	3.2	34
246	Time-resolved photoluminescence and steady-state optical investigations of a Zn _{1-x} Cd _x Se/ZnSe quantum well. Nuovo Cimento Della Societa Italiana Di Fisica D - Condensed Matter, Atomic, Molecular and Chemical Physics, Biophysics, 1995, 17, 1435-1440.	0.4	3
247	Current Activity in CNRS-Sophia Antipolis Regarding Wide-Gap II-VI Materials. Physica Status Solidi (B): Basic Research, 1995, 187, 457-466.	1.5	9
248	Defect control during growth of highly mismatched (100). Journal of Crystal Growth, 1995, 146, 368-373.	1.5	24
249	Surfactant-mediated molecular-beam epitaxy of III-V strained-layer heterostructures. Journal of Crystal Growth, 1995, 150, 460-466.	1.5	39
250	Aspects of low heterostructure symmetry in (311)A (In,Ga)As/GaAs. Journal of Crystal Growth, 1995, 150, 482-486.	1.5	2
251	Novel plastic strain-relaxation mode in highly mismatched III-V layers induced by two-dimensional epitaxial growth. Applied Physics Letters, 1995, 66, 2265-2267.	3.3	63
252	Structural characterization of lattice matched Al _x In _{1-x} As/InP and Ga _y In _{1-y} As/InP heterostructures by transmission electron microscopy and high-resolution x-ray diffraction. Journal of Applied Physics, 1995, 78, 2403-2410.	2.5	12

#	ARTICLE	IF	CITATIONS
253	Temperature dependence of the photoluminescence of Zn _{1-x} Cd _x Se/ZnSe strained-layer quantum wells. <i>Applied Physics Letters</i> , 1995, 67, 103-105.	3.3	24
254	Double period RHEED oscillations during MBE growth of GaAs and AlAs on the GaAs(110) surface. <i>Surface Science</i> , 1995, 331-333, 479-484.	1.9	6
255	Le laser bleu : État de l'art. <i>Annales De Physique</i> , 1995, 20, 743-750.	0.2	1
256	Interplay between Surface Stabilization, Growth Mode and Strain Relaxation during Molecular-Beam Epitaxy of Highly Mismatched III-V Semiconductor Layers. <i>Europhysics Letters</i> , 1994, 25, 663-668.	2.0	28
257	Growth mechanism of GaAs on (110) GaAs studied by high-energy electron diffraction and atomic force microscopy. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1994, 12, 2574.	1.6	24
258	Tunable generation of nanometer-scale corrugations on high-index III-V semiconductor surfaces. <i>Physical Review B</i> , 1994, 49, 11053-11059.	3.2	8
259	Time-resolved investigations of excitonic recombination in highly strained InAs/Al _{0.48} In _{0.52} As quantum wells. <i>Journal of Applied Physics</i> , 1994, 76, 618-620.	2.5	2
260	Strained InAs/Ga _{0.47} In _{0.53} As quantum-well heterostructures grown by molecular-beam epitaxy for long-wavelength laser applications. <i>Solid-State Electronics</i> , 1994, 37, 1311-1314.	1.4	7
261	Surface stoichiometry, epitaxial morphology and strain relaxation during molecular beam epitaxy of highly strained InAs/Ga _{0.47} In _{0.53} As heterostructures. <i>Journal of Crystal Growth</i> , 1994, 135, 97-112.	1.5	28
262	Surfactant-mediated molecular beam epitaxy of strained layer semiconductor heterostructures. <i>Thin Solid Films</i> , 1993, 231, 43-60.	1.8	81
263	Determination of the Sb composition profile in MBE-grown GaSb/GaAs structures by high-resolution X-ray diffractometry. <i>Journal of Crystal Growth</i> , 1993, 127, 503-507.	1.5	3
264	Virtual-surfactant epitaxy of InAs quantum wells. <i>Journal of Crystal Growth</i> , 1993, 127, 765-769.	1.5	17
265	Strained InAs/Al _x Ga _{0.48-x} In _{0.52} As heterostructures: a tunable quantum well materials system for light emission from the near-IR to the mid-IR. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 1993, 21, 288-292.	3.5	0
266	Low-density band-filling in strained InAs quantum wells. <i>Applied Physics A: Materials Science and Processing</i> , 1993, 56, 109-112.	2.3	4
267	Virtual-surfactant-induced wetting in strained-layer heteroepitaxy. <i>Applied Physics A: Solids and Surfaces</i> , 1993, 56, 91-94.	1.4	15
268	Overlayer strain: A key to directly tune the topography of high-index semiconductor surfaces. <i>Applied Physics Letters</i> , 1993, 63, 3300-3302.	3.3	13
269	Optical properties of InAs quantum wells emitting between 0.9 μ m and 2.5 μ m. <i>Semiconductor Science and Technology</i> , 1993, 8, S236-S239.	2.0	9
270	Surface stoichiometry and interface formation during molecular-beam epitaxy of strained InAs/Al _x Ga _{0.48-x} In _{0.52} As heterostructures. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1993, 11, 1388.	1.6	4

#	ARTICLE	IF	CITATIONS
271	Analysis of epitaxial $GaxIn1-xAs/InP$ and $AlyIn1-yAs/InP$ interface region by high resolution x-ray diffraction. Applied Physics Letters, 1993, 62, 149-151.	3.3	18
272	Virtual-surfactant epitaxy of strained $InAs/Al_{0.48}In_{0.52}As$ quantum wells. Applied Physics Letters, 1993, 62, 858-860.	3.3	28
273	Surfactant-Mediated MBE of Strained-Layer III-V Semiconductor Heterostructures. Solid State Phenomena, 1993, 32-33, 129-140.	0.3	1
274	Long-wavelength strained-layer $InAs/GaInAs$ single-quantum-well laser grown by molecular beam epitaxy on InP substrate. Electronics Letters, 1993, 29, 1255.	1.0	13
275	Observation of $InGaAs / InAlAs$ Surface Quantum Wells by Photoreflectance and Photoluminescence Excitation Spectroscopies. Materials Research Society Symposia Proceedings, 1993, 326, 127.	0.1	1
276	Strained $InAs/Al_xGa_{0.48-x}In_{0.52}As$ heterostructures: a tunable quantum well materials system for light emission from the near-IR to the mid-IR. European Materials Research Society Symposia Proceedings, 1993, 40, 288-292.	0.0	0
277	Photoluminescence of virtual-surfactant grown $InAs/Al_{0.48}In_{0.52}As$ single quantum wells. Applied Physics Letters, 1992, 60, 2877-2879.	3.3	43
278	$InAs/Ga_{0.47}In_{0.53}As$ quantum wells: A new III-V materials system for light emission in the mid-infrared wavelength range. Applied Physics Letters, 1992, 61, 2808-2810.	3.3	29
279	Strained $InAs$ single quantum wells embedded in a $Ga_{0.47}In_{0.53}As$ matrix. Applied Physics Letters, 1992, 61, 846-848.	3.3	19
280	Structural properties and transport characteristics of pseudomorphic $GaxIn1-xAs/AlyIn1-yAs$ modulation-doped heterostructures grown by molecular beam epitaxy. Journal of Applied Physics, 1992, 71, 1790-1797.	2.5	9
281	Liquid phase epitaxy and characterization of $InAs_{1-x-y}Sb_xP_y$ on (100) $InAs$. Journal of Crystal Growth, 1992, 121, 463-472.	1.5	24
282	High-quality $Al_{0.48}In_{0.52}As$ grown by molecular beam epitaxy at high InP -substrate temperature. Materials Letters, 1991, 11, 343-347.	2.6	3
283	Structural and optical properties of $Al_{0.48}In_{0.52}As$ layers grown on InP by molecular beam epitaxy: Influence of the substrate temperature and of a buffer layer. Journal of Applied Physics, 1991, 70, 7362-7369.	2.5	49
284	Préparation et Étude de diodes laser à $GaInAsSb-GaAlAsSb$ fonctionnant en continu à 80K. Journal De Physique III, 1991, 1, 605-622.	0.3	0
285	Growth by liquid phase epitaxy and characterization of $GaInAsSb$ and $InAsSbP$ alloys for mid-infrared applications (2-3 μm). , 1991, , .		10
286	Growth limitations by the miscibility gap in liquid phase epitaxy of $Ga_{1-x}In_xAs_ySb_{1-y}$ on $GaSb$. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1991, 9, 125-128.	3.5	26
287	$GaInAsSb/GaSb$ pn photodiodes for detection to 2.4 μm . Electronics Letters, 1991, 27, 1237.	1.0	27
288	High temperature liquid phase epitaxy of (100) oriented $GaInAsSb$ near the miscibility gap boundary. Journal of Crystal Growth, 1990, 104, 683-694.	1.5	40

#	ARTICLE	IF	CITATIONS
289	2.5 μ m GaInAsSb lattice-matched to GaSb by liquid phase epitaxy. Journal of Applied Physics, 1990, 68, 5936-5938.	2.5	36
290	New III-V double-heterojunction laser emitting near 3.2 μ m. Electronics Letters, 1988, 24, 1542.	1.0	23
291	Characteristic temperature T_0 of Ga _{0.83} In _{0.17} As _{0.15} Sb _{0.85} /Al _{0.27} Ga _{0.73} As _{0.02} Sb _{0.98} injection lasers. Electronics Letters, 1988, 24, 1076.	1.0	12
292	Control of the polarity of GaN epilayers using a Mg adsorption layer. , 0, , .		0
293	Correlations between growth mode and structural and optical properties of GaInNAs quantum wells grown by MBE. , 0, , .		0